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APPLICANT: Sadeg M. Faris)
SERIAL NO.: 10/719,663) Group Art Unit
FILING DATE: November 20, 2003) 2818
FOR: Method of Fabricating Multi Layer) Examiner
Devices on Buried Oxide Layer Substrates) Nguyen, Dao H

JUL 07 2006

Commissioner of Patents
PO Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

In accordance with the provisions of 37 CFR 1.97, 1.98 AND 1.99, Applicants submit herewith an Information Disclosure Statement in order to fulfill Applicants' duty as set forth in 37 CFR 1.56.

☐ The Information Disclosure Statement submitted herewith is being filed within three months of the filing date of a national application other than a continued prosecution application under 37 CFR 1.53(d)

☐ The Information Disclosure Statement submitted herewith is being filed within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application.

☒ The Information Disclosure Statement submitted herewith is being filed before the mailing of a first Office action on the merits; or before the mailing of a first Office action after the filing of a request for continued examination under 37 CFR 1.114

☐ The Information Disclosure Statement submitted herewith is being filed before the mailing date of (a) final action under 37 CFR 1.113, (b) notice of allowance under 37 CFR 1.311, or (c) action that otherwise closes prosecution in the application and is accompanied by (a) the statement specified in 37 CFR 1.97(e) or (b) the fee set forth in 37 CFR 1.17(p).

☐ The Information Disclosure Statement submitted herewith is being filed on or before payment of the issue fee and is accompanied by (a) the statement specified in 37 CFR 1.97(e) and (b) the fee set forth in 37 CFR 1.17(p).

☐ The Commissioner is hereby authorized to charge the fee of \$180.00 to Deposit Account No. _____.

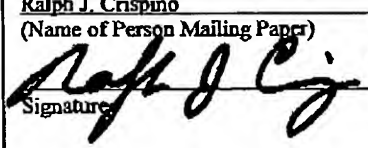
In accordance with new USPTO procedure, copies of U.S. references are not transmitted.

Further, Applicants respectfully request that the voluminous copies of the foreign references and the non-patent literature cited in related application serial no. 09/950,909 be used for the examination of this application. If this is not acceptable, kindly contact the undersigned as soon as possible so the references may be submitted,

By:


Ralph J. Crispino
Registration No. 46,144

July 7, 2006
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	Examiner Name	Nguyen, Dao H
Sheet 1 of 6	Attorney Docket Number	Reveo-0202USAAON00

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		4,370,176	25-Jan-83	Bruel	148	1.5	
		4,371,421	01-Feb-83	Fan et al.	156	624	
		4,471,003	11-Sep-84	Cann	427	34	
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		4,816,420	28-Mar-89	Bozler et al.	437	2	
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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
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